

ADVANCED IC SUBSTRATES FOR HETEROGENEOUS INTEGRATION

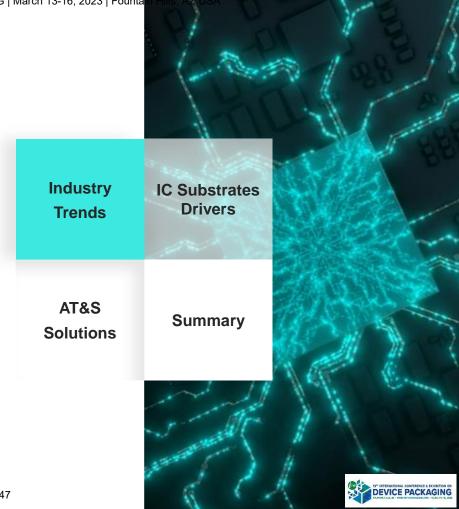
Markus Leitgeb, Venkata Mokkapati, Rozalia Beica R&D, BU Microelectronics

March 15, 2023





PRESENTATION OUTLINE



DIGITALIZATION EVERYWHERE

Data driven society

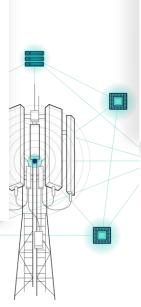
THE RISE OF THE DATA ERA

Global Data Volume:

2020: 59 Zetabyte

2025: 175 Zetabyte

→ (24% CAGR)



Autonomous **Driving**

Cameras, Lidar, Radar

Climate Research

Data generation and analytics

Genomics

High performance computing for human genome sequencing

Vision Processor

Augmented reality applications

DEVICE PACKAGING

Source: IDC (2019, 2020)

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DATA GROWTH DRIVES COMPUTE, STORAGE, CONNECTIVITY & NETWORKING DEMAND

- Technology changes
- Increased packaging solutions at system level
- There is NO standard technology which serves all application or customer needs and architecture.
- New module & system in packages driven by multiple new disruptive technologies

"We are at the tip of an iceberg where we can go with packaging"

Babak Sabi – Intel Corporate VP Assembly and Test Technology Development Intel

Data storage

Server farms / data centers (e.g. server substrates)

- Solutions for increasing data speed (50gbit/second+)
- Reduced power consumption
- High level of integration and miniaturization

Data transfer

Antennas (e.g. antenna modules, RF-modules, 5G communication, Car2Car, V2X)

- High end technologies for best in class signal integrity
- Low latency
- Higher bandwidth with new technical concepts

Data generation

Sensors (e.g. mainboard, substrates for edge- & cloud computing)

- Ever-smaller L/S through innovative production processes (mSAP)
- Miniaturization and increased functionalities
- 140 GHz solutions for next generation radar applications

Data processing & analytics

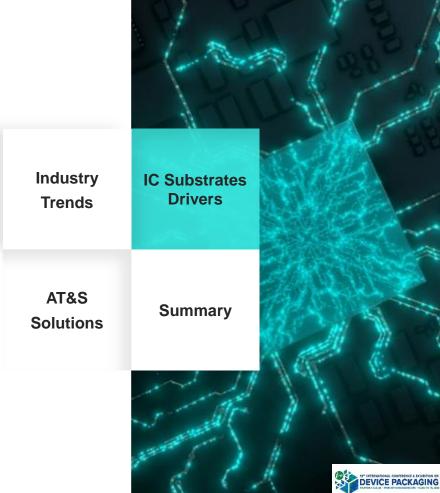
Devices (e.g. mainboard, substrates for edge- & cloud computing)

- Ever-smaller form factors
- Integration of advanced active and passive RF components
- High end technologies for best in class signal integrity



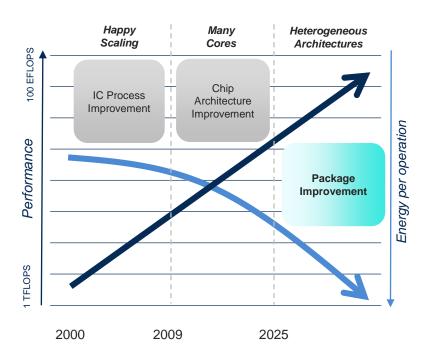


PRESENTATION OUTLINE



FUTURE TREND FOR ADVANCED COMPUTING

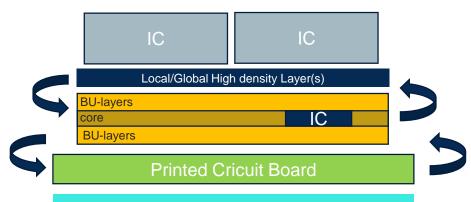
Node scaling alone does not provide desired performance



Advanced Substrates & Packaging

New Challenging Functions in Packaging

- Larger Body Sizes (Chiplets, HIR)
- CTE Mismatch (Chiplets, Interposer)
- D2D Connection (BW, low latency)
- Power Delivery (Power Mgmt./conversion)
- Thermal Dissipation (Efficient Cooling)



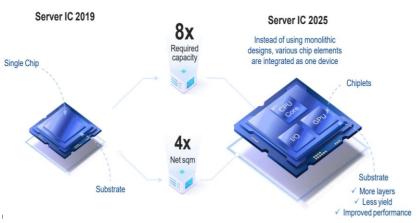
AT&S

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Which functions can/should be optimized where in the Package?

ABF SUBSTRATES DRIVERS

FCBGA Development trends



Drivers	Requirement trends
Heterogeneous integration	Large body/package size (up to 100x100)
High I/o COUNT	High layer count >20L
High-density interconnect	L/S 9/12µm
Bump pitch	90µm and below
Increase bandwidth	High-speed transmission
Increase assembly yield	Low warpage
More functionalities	Thermal management

What else can be done with IC Substrates?



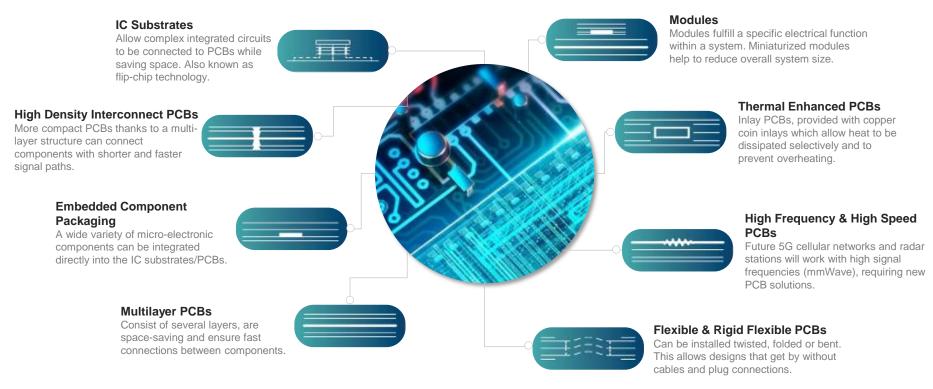


PRESENTATION OUTLINE



AT&S PRODUCT PORTFOLIO

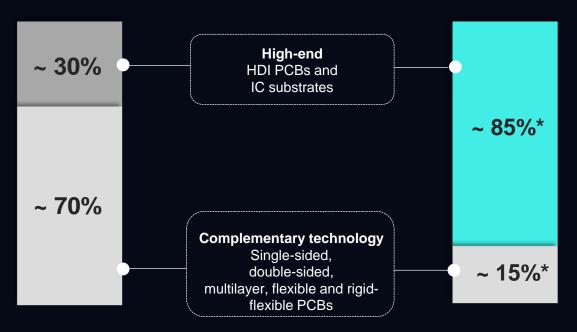
Wide range of products for interconnection solutions

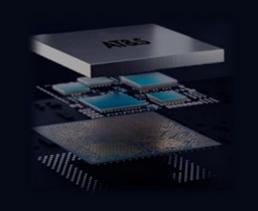






STRATEGIC FOCUS ON HIGH-END TECHNOLOGIES





General PCB and IC substrates market

AT&S revenue

R&D PROGRAMS FOCUSING ON THE MAJOR TRENDS

Innovation focused on major trends and industry needs



Miniaturization

Increased computing power for fast data processing



Modularization

More functionality at same or reduced space



Increased speed / Low latency

Communication of high data volumes (5G, Autonomous Driving)



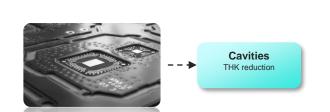
Increased power / Power efficiency

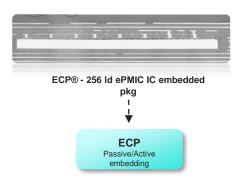
Reducing non-value adding electrical loss

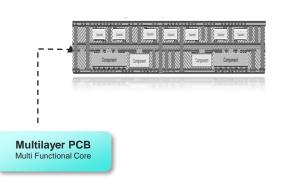


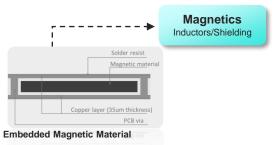


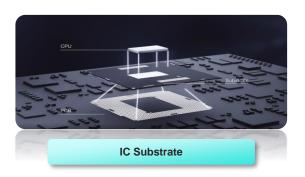
ADVANCED PACKAGING CONCEPTS ON LARGE PANELS

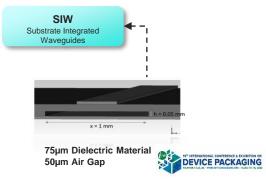








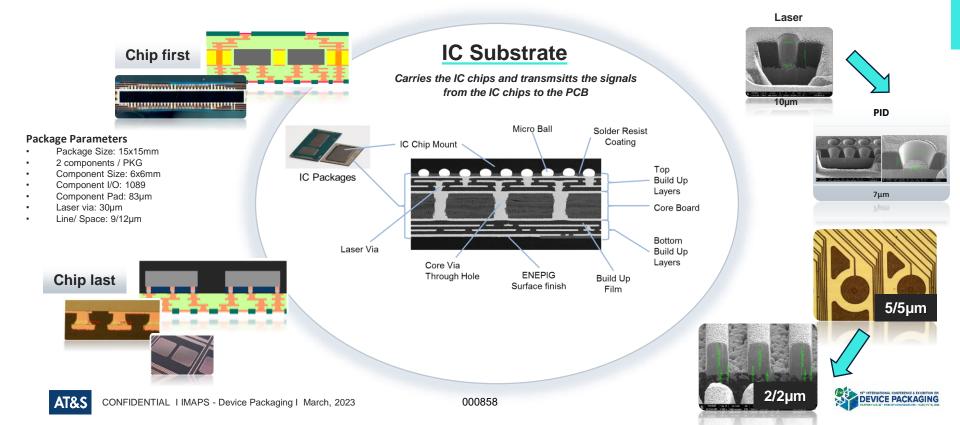




MINIATURIZATION & MODULARIZATION

Novel Packaging Concepts

Small Via and High Density Routing



EMBEDDING OF COMPONENTS

Reliability test TV : MRT 10x, TCT 750cycle and uHAST 100hr → No blister/delamination, R shift < 6%

General package information:

• 6 Layer

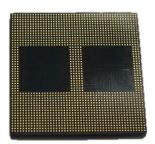
• L/S: 9/12µm

Via: 30µm

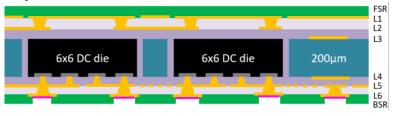
Core thickness: 200µm

• 2 dies embedded





Symmetric BU: n-2-n structure with ECP®



MSL3(Pre-condition), MRT 10X, TCT 750 cycles & uHAST test results: Passed

Test item	Standard	Failure mode Pre-conditioning		Rel. Conditions	
Multi Reflow	IPC/JEDEC J-STD-020D.1	Visual check Cross section analysis E-test		Reflow peak max 260°C, 10x (10 reflow cycles)	
тст	IPC TM650 2.6.2.7	Visual check Cross section analysis E-test	125°C 24hrs, 60°C/60%RH for 40hrs, 3x Reflow(260°C peak)	-55℃/+125℃, 750cycle (Readout at 250/500/750)	
uHAST	JEDEC JESD22-A110E	Visual check Cross section analysis E-test		130℃/85%RH, 100hr (Readout at 50/100)	

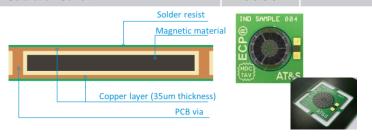


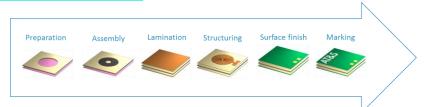
Source: AT&S AG

EMBEDDING OF MAGNETIC MATERIALS

- Qualified process based on the ECP® technology
- Independent from layer count
- Can be applied to PCBs and Cores of ICS

Inductor	Value	Unit
Cu THK	35	μm
Magnetic Material THK	0.3	mm
Inner/outer diameter	3/10.5	mm
Windings	16	turns
Total thickness	0.5	mm
Inductance	5.7-1.15	μH
Saturation Current	0.3-3.6	Α





Parameter	Symbol	Without air gap	With 1 air gap	With 3 air gaps	Standard SMD (2)	Benchmar k
Inductance	L (@ 1 MHz)	5.7 μH	2.2 µH	1.15 µH	1.2 µH	Equal
Saturation current	I _{sat} (1)	300 mA	1.5 A	3.6 A	3.8 A	Equal
Rated current (DC)	I _R (@ ΔT = 40 K)		2.0 A		1.9 A	Equal
DC Resistance	R _{DC} (@ 0.1 A)	79 mΩ		82 mΩ	Equal	
Self-resonance fr.	f _{res}	30 MHz	40 MHz	80 MHz	75 MHz	Equal
Package size	D _I /D _O		3/10.5 mm		2.5 x 2 mm	
Air gap length	<u>l</u> g	-	500 μm	3 x 170 μm	-	
Total thickness	h		500 μm		1 mm	↑
		Ţ			(1) A (2) ¥	nductance drops 30% @ Isat Wirth Electronics (74438323012)
	Without air g	15 2.0 2.5 3.0 arrent [A]	With one air ga 2.3 8 0 1.3 1.0 1.0 0 0 0 1.0 1.0 0 0 0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0	5 20 25 30	With three air gaps 1.4 1.2 3.1 3.1 3.0 4.0 0.0 0.0 0.0 0.0 1.0 1.1 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0	25 20

Source: AT&S AG



CONCETS FOR LOSS REDUCTION

Solutions to improve Signal Integrity Performance

Loss factor Base Material (Dielectric Losses)

Suitable Materials

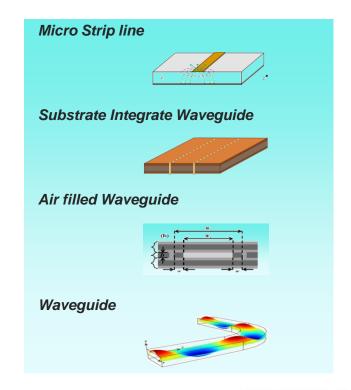
Length of Traces (Conductor Losses)

Miniaturization (L/S)

Skin Effect (Ohmic load)

- Low Copper Foil Treatment (low / no profile)
- Smooth Traces (Adhesion Promoter)
- Suitable End Surface Platings (Ni less ...)







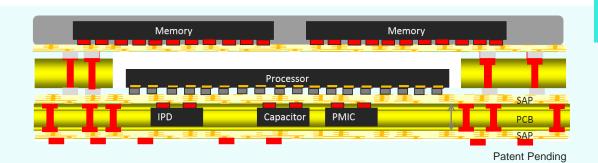


COMBINATION OF DIFFERENT CONCEPTS

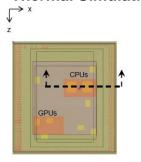
Chip First + Chip last + AirGap

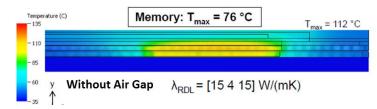
Computing/Processing Module with:

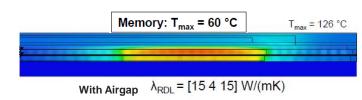
- Integrated power supply
- Solution to connect processor and memory in a PoP structure (if needed)
- Integrated signal stabilization
- Potential for additional functionality (communication, anti-fraud, etc.)
- Improved Thermal Management



Thermal Simulation







Conditions in package improved due to air gap

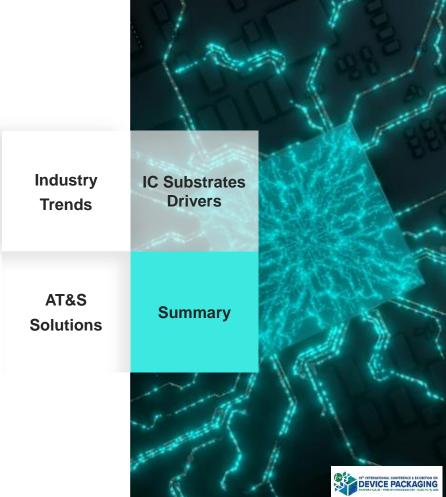
- Temperature of memory decreases (76°C to 60°C)
- Temperature of Processor increases (112°C to 126°C) → can be decreased with tool box

Source: AT&S AG

19" INTERNATIONAL CONFERENCE A EXHIBITION ON DEVICE PACKAGING



PRESENTATION OUTLINE



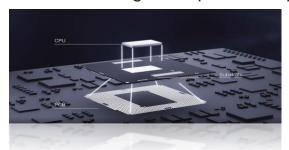
SUMMARY & CONCLUSION

New Interconnect Requirements drive Advance Packaging Solutions

- Increased packaging solutions at system level integration are required
- Miniaturization of electronic systems drives the need for larger, multi-functional modules
- The IC Substrate is a major building block in nearly all advanced system architectures

PCB/IC Substrate Technologies offer a versatile Tool Box

- Fan-Out capabilities for fine pitch components enable chip first and chip last integration
- Magnetic materials can be embedded for various functions (Inductor, shielding, etc.)
- New concepts offer improved Signal Integrity
- Advanced Cooling concepts use Copper plated vias, cavity walls and inlays



CONFIDENTIAL I IMAPS - Device Packaging I March, 2023









THANK YOU!

For more information:

R&D Collaboration:

Markus Leitgeb <u>m.leitgeb@ats.net</u>

Business Development:

Venkata Mokkapati v.mokkapati@ats.net

Industry **IC Substrates Drivers Trends** AT&S **Summary Solutions** DEVICE PACKAGING

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